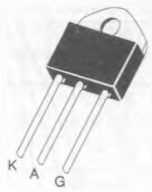
SGS-THOMSON MICROELECTRONICS

BTW69-200N → 1200N

THYRISTORS

- GLASS PASSIVATED CHIP
- HIGH STABILITY AND RELIABILITY
- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- EASY MOUNTING ON HEATSINK



TOP 3
(Plastic)

DESCRIPTION

General purpose SCR suited for power supplies up to 400 Hz on resistive or inductive loads.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		BTW69-200N → 800N	BTW69-1000N/1200N	Unit
$I_{T(RMS)}$	RMS on-state Current (1)	T_c = 70 °C	55		A
$I_{T(AV)}$	Mean on-state Current (1)	T_c = 70 °C	35		A
I_{TSM}	Non Repetitive Surge Peak on-state Current (T_j initial = 25 °C) (2)	t = 8.3 ms	525	420	A
		t = 10 ms	500	400	
I^2t	I^2t Value for Fusing	t = 10 ms	1250	800	A^2s
di/dt	Critical Rate of Rise of on-state Current (3)		100		A/µs
T_{stg} T_j	Storage and Operating Junction Temperature Range		– 40 to 125 – 40 to 125		°C °C

Symbol	Parameter	BTW69-						Unit
		200N	400N	600N	800N	1000N	1200N	
V_{DRM} V_{RRM}	Repetitive Peak off-state Voltage (4)	200	400	600	800	1000	1200	V

(1) Single phase circuit, 180° conduction angle.
(2) Half sine wave.
(3) I_G = 800 mA di_G/dt = 1 A/µs.
(4) T_j = 125 °C.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th\ (j-c)}$	Junction-case for D.C.	0.87	°C/W
$R_{th\ (c-h)}$	Contact (case to heatsink)	0.20	°C/W

GATE CHARACTERISTICS (maximum values)

P_{GM} = 50 W (t_p = 10 µs) I_{FGM} = 2 A (t_p = 10 µs) V_{RGM} = 5 V

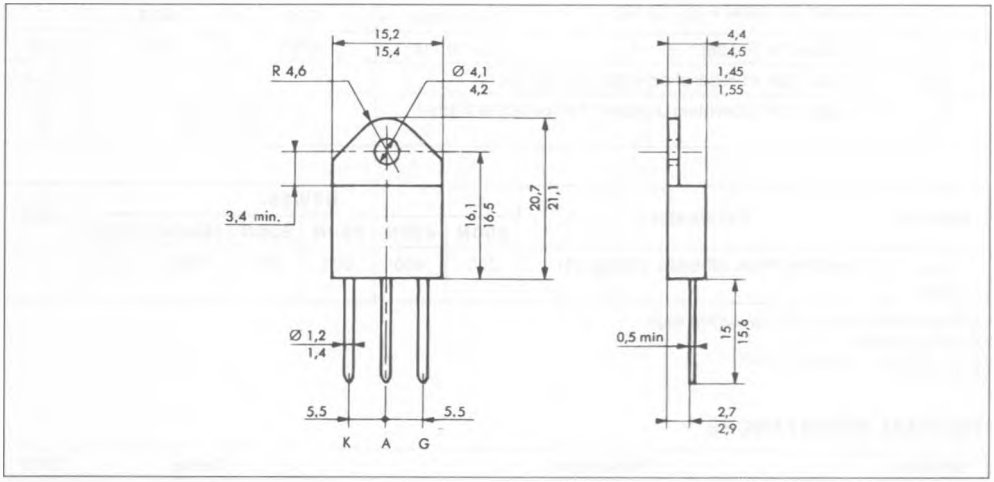
$P_{G(AV)}$ = 1 W V_{FGM} = 15 V (t_p = 10 µs)

ELECTRICAL CHARACTERISTICS

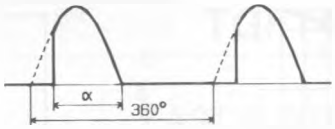
Symbol	Test Conditions			Min.	Typ.	Max.	Unit
I_{GT}	T_j = 25 °C Pulse Duration > 20 µs	V_D = 12 V	R_L = 33 Ω			80	mA
V_{GT}	T_j = 25 °C Pulse Duration > 20 µs	V_D = 12 V	R_L = 33 Ω			1.5	V
V_{GD}	T_j = 125 °C	$V_D = V_{DRM}$	R_L = 3.3 kΩ	0.2			V
I_H	T_j = 25 °C	I_T = 0.5 A	Gate Open		20	150	mA
I_L	T_j = 25 °C Pulse Duration > 20 µs	V_D = 12 V	I_G = 160 mA		40		mA
V_{TM}	T_j = 25 °C	I_{TM} = 110 A	t_p = 10 ms			2	V
I_{DRM}	V_{DRM} Specified		T_j = 25 °C			0.02	mA
			T_j = 125 °C			6	
I_{RRM}	V_{RRM} Specified		T_j = 25 °C			0.02	mA
			T_j = 125 °C			6	
t_{gt}	T_j = 25 °C I_G = 200 mA	$V_D = V_{DRM}$ di_G/dt = 0.2 A/µs	I_T = 110 A		2		µs
t_q	T_j = 125 °C V_D = 67 % V_{DRM} Gate Open	I_T = 110 A di/dt = 30 A/µs	V_R = 75 V dv/dt = 20 V/µs		100		µs
dv/dt*	T_j = 125 °C Linear Slope up to V_D = 67 % V_{DRM}	Gate Open	$V_{DRM} \leq$ 800 V	500			V/µs
			$V_{DRM} \geq$ 1000 V	250			

* For higher guaranteed values, please consult us.

PACKAGE MECHANICAL DATA : TOP 3 Plastic



Cooling method : by conduction (method C)
Marking : type number
Weight : 5 g.



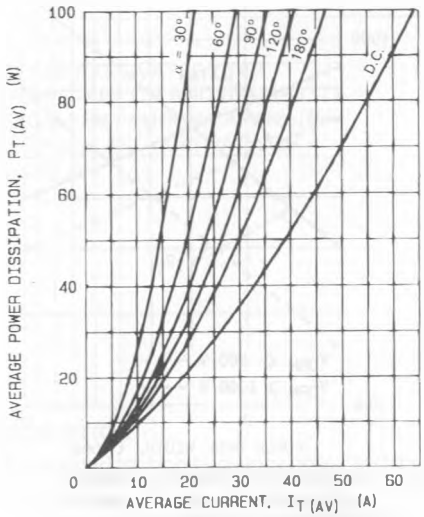


FIG.1 - MAXIMUM ON-STATE POWER DISSIPATION FOR SINUSOIDAL CURRENT WAVEFORM

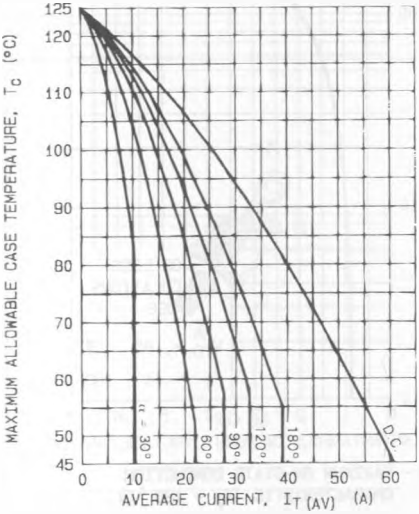
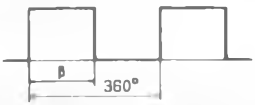


FIG.2 - MAXIMUM ALLOWABLE CASE TEMPERATURE FOR SINUSOIDAL CURRENT WAVEFORM



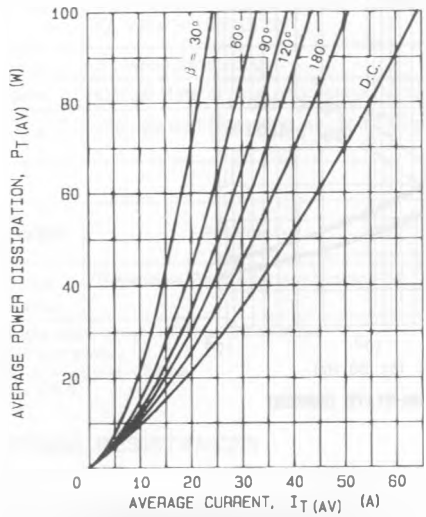


FIG.3 - MAXIMUM ON-STATE POWER DISSIPATION FOR RECTANGULAR CURRENT WAVEFORM

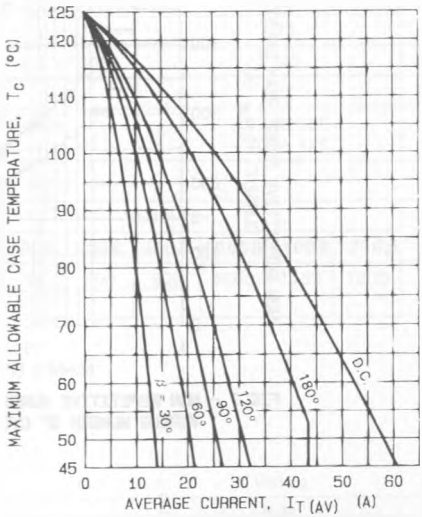


FIG.4 - MAXIMUM ALLOWABLE CASE TEMPERATURE FOR RECTANGULAR CURRENT WAVEFORM

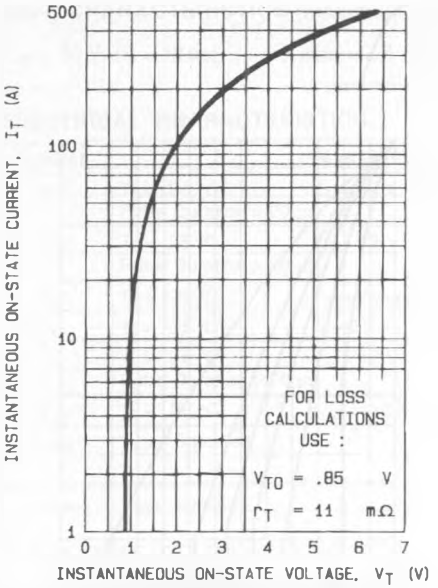


FIG.5 - MAXIMUM ON-STATE CONDUCTION CHARACTERISTIC (T_J = 125 °C).

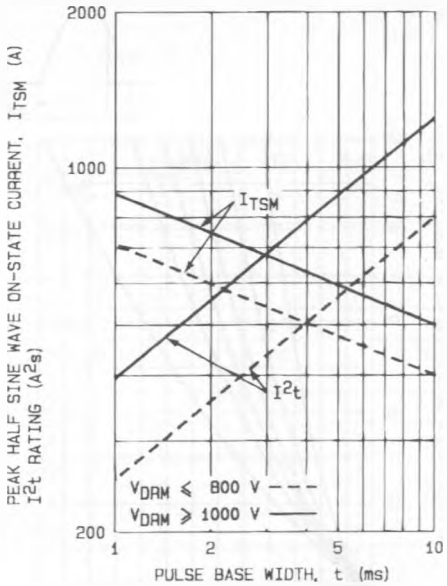


FIG.6 - NON REPETITIVE SUB-CYCLE SURGE ON-STATE CURRENT AND I^2t RATING (INITIAL T_J = 25 °C).

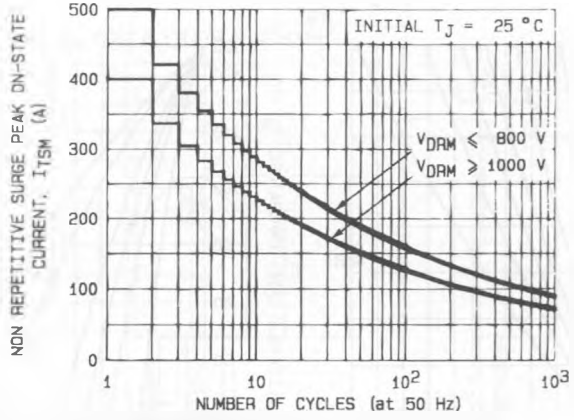


FIG.7 - NON REPETITIVE SURGE PEAK ON-STATE CURRENT VERSUS NUMBER OF CYCLES.